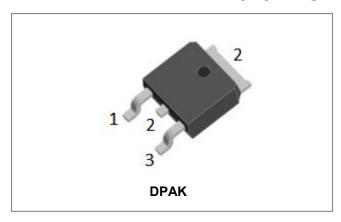






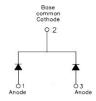
## MBRD1545CT SCHOTTKY RECTIFIER



#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- "-A" is an AEC-Q101 qualified device
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

### Maximum Ratings@T<sub>A</sub>=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$			
Working Peak Reverse Voltage	$V_{RWM}$	-	45	V
DC Blocking Voltage	$V_R$			
Average Rectified Forward Current	I=	50% duty cycle @Tc=105°C,	7.5(Peg Leg)	۸
Average Rectilled Forward Current	IF (AV)	rectangular wave form	15(Peg Device)	A
Peak One Cycle Non-Repetitive Surge Current(peg leg)	I <sub>FSM</sub>	8.3 ms, half Sine pulse	150	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V <sub>F1</sub>	@ 7.5A, Pulse, T <sub>J</sub> = 25 °C	0.49	0.65	V
(Peg Leg) *	$V_{F2}$	@ 7.5A, Pulse, T <sub>J</sub> = 125 °C	0.42	0.60	V
Reverse Current (Peg Leg) *	I <sub>R1</sub>	I <sub>R1</sub> @V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C		1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	15	20	mA
Junction Capacitance(Peg Leg)	$C_T$ @V <sub>R</sub> = 5V, $T_C$ = 25 °C, $f_{SIG}$ = 1MHz 300		400	pF	

<sup>\*</sup> Pulse width < 300 μs, duty cycle < 2%



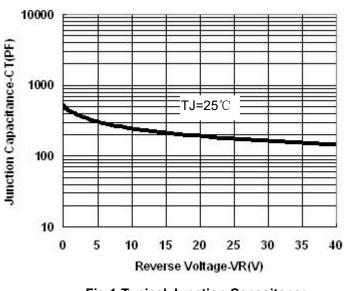




## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	abol Condition Specification		
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to + 150	°C
Typical Thermal Resistance Junction to Case(Peg Leg)	R <sub>θ</sub> JC	-	3.5	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

## **Ratings and Characteristics Curves**



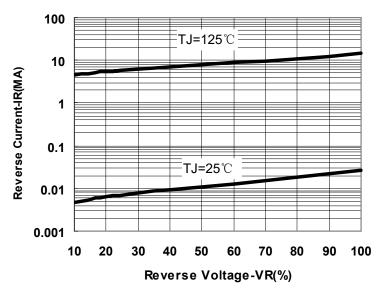


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

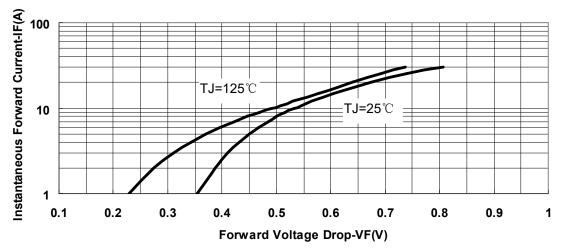


Fig.3-Typical Instantaneous Forward Voltage Characteristics

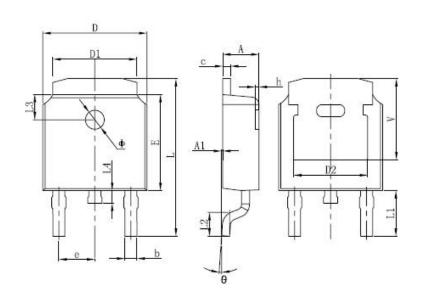
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### **Mechanical Dimensions DPAK**



Symbol	Dimensions in millimeters			
Symbol	Min.	Typical	Max.	
Α	2.18	-	2.39	
A1	-	-	0.13	
b	0.64	-	0.89	
С	0.46	-	0.89	
D	6.35	-	6.73	
D1	4.95	-	5.46	
D2	4.32	-	-	
E	5.97	6.1	6.22	
е	2.29BSC			
L	9.4	-	10.41	
L1	2.90 REF.			
L2	1.4	1.52	1.78	
L3	1.60 REF.			
L4	-	-	1.02	
Ф	1.1	_	1.3	
Θ	0°	-	10°	
V	5.21	-	-	

# **Ordering Information**

Device	Package	Shipping
MBRD1545CT	DPAK (Pb-Free)	2500pcs / reel
MBRD1545CTTR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

# **Marking Diagram**



Where XXXXX is YYWWL

 MBR
 = Device Type

 D
 = Package type

 15
 = Forward Current (15A)

 45
 = Reverse Voltage (45V)

 CT
 = Configuration

 SSG
 = SSG

 YY
 = Year

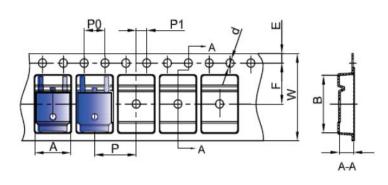
 WW
 = Week

= Lot Number

Epoxy resin UL:94V-0

Cautions: Molding resin

# **Carrier Tape Specification DPAK**



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

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